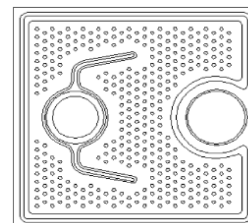




## ELC-405-34

- VIOLET LED bare chip die
- 405 nm, 30 mW
- 315x315x120  $\mu\text{m}$
- GaN structure
- P + N up

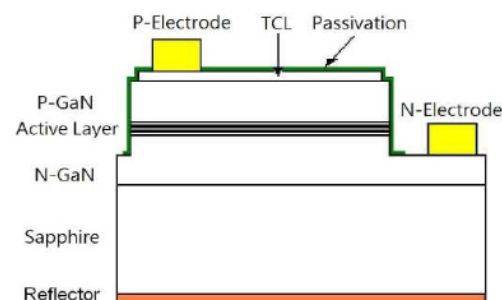


## Description

ELC-405-34 is a VIOLET LED bare chip die on sapphire substrate with GaN based epitaxial layers, backside DBG (distributed bragg reflector) coating, and 80  $\mu\text{m}$  Au alloy bonding pads. It is typically emitting at 405 nm with an optical output power of 30 mW. ELC-405-34 is packed on adhesive film with wire-bond side on top

## Maximum Rating ( $T_{\text{CASE}} = 25^{\circ}\text{C}$ )

Parameter	Symbol	Values		Unit
		Min.	Max.	
Forward Current*	$I_F$		30	mA
Reverse Voltage	$V_R$		5.0	V
Junction Temperature	$T_J$		+ 115	$^{\circ}\text{C}$
Operating Temperature	$T_{\text{OP}}$	- 40	+ 85	$^{\circ}\text{C}$
Storage Temperature	$T_{\text{STG}}$	+ 7	+ 35	$^{\circ}\text{C}$



## Electro-Optical Characteristics ( $T_{\text{CASE}} = 25^{\circ}\text{C}$ , $I_F = 20 \text{ mA}$ )

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Peak Wavelength	$\lambda_P$	400	405	410	nm
Spectral Width (FWHM)	$\Delta\lambda$			30	nm
Forward Voltage	$V_F$			3.5	V
Reverse Current ( $V_R = 5\text{V}$ )	$V_R$			1	$\mu\text{A}$
Output Power	$P_O$	28	30	32	mW

